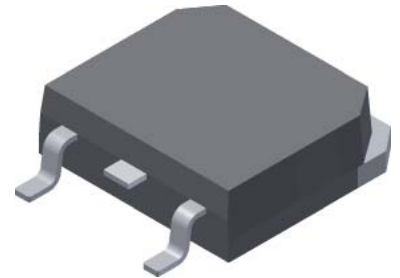


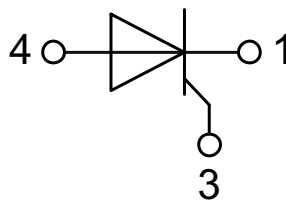
# High Voltage Phase Control Thyristor

$$V_{\text{DRM}} = 2500 \text{ V}$$

$$I_{\text{TSM}} = 200 \text{ A}$$



Backside = anode



### Features / Advantages:

- high voltage thyristor
  - for line frequency
  - chip technology for long term stability
  - planar glass passivated

### Applications:

- controlled rectifiers
  - power supplies
  - drives
- AC switches
- capacitor discharge control
  - flash tubes
  - X-ray and laser generators

### Package: TO-268AA (D<sup>3</sup>Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

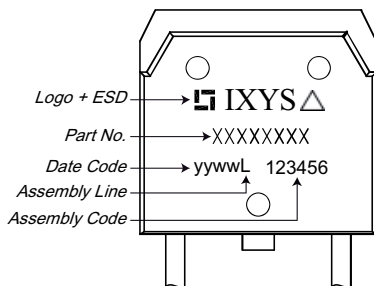
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).



Rectifier			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
$V_{DRM/DSM}$	max. repetitive/non-repetitive forward blocking voltage				2500	V
$V_{RRM/RSM}$	max. repetitive/non-repetitive reverse blocking voltage				1650	V
$I_{RRM/DRM}$	max. repetitive off-state current	$V_R = V_{RRM}$ $V_D = V_{DRM}$			50 200	$\mu$ A $\mu$ A
$I_{DSM/RSM}$	max. non-repetitive off-state current	$V_R = V_{RSM}; V_D = V_{DSM}$			2	mA
$I_{TSM}$	max. forward surge current	$t = 10$ ms, sine; $V_R = 0$ V			200	A
$(di/dt)_{cr}$	critical rate of rise of current	$f = 50$ Hz; $t_p = 200$ $\mu$ s; $V_D = 2000$ V $di_G/dt = 0.45$ A/ $\mu$ s; $I_G = 0.45$ A non repetitive; $I_T = 45$ A			150	A/ $\mu$ s
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = 2200$ V $R_{GK} = \infty$ ; method 1 (linear voltage rise)			5000	V/ $\mu$ s
$V_T$	forward voltage drop	$I_T = 45$ A			3.0	V
$V_{GT}$ $I_{GT}$	gate trigger voltage gate trigger current	$V_D = 6$ V			2.5 250	V mA
$V_{GD}$ $I_{GD}$	gate non-trigger voltage gate non-trigger current	$V_D = 2/3 V_{DRM}$			0.2 5	V mA
$I_L$	latching current	$t_p = 10$ $\mu$ s; $V_D = 6$ V $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ $\mu$ s			700	mA
$I_H$	holding current	$V_D = 6$ V; $R_{GK} = \infty$			300	mA
$t_q$	turn-off time	$V_R = 10$ V; $I_T = 20$ A; $V_D = 800$ V $di/dt = -20$ A/ $\mu$ s; $dv/dt = 20$ V/ $\mu$ s $t_p = 300$ $\mu$ s			100	$\mu$ s
$R_{thJC}$	thermal resistance junction to case				0.8	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.15	K/W

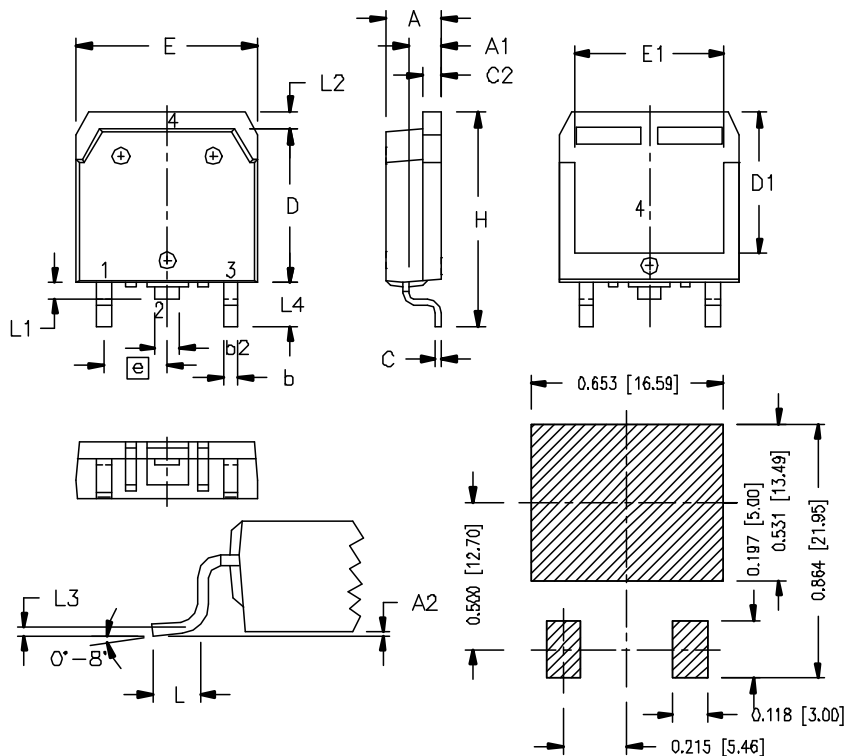
Package TO-268AA (D <sup>3</sup> Pak)			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-10		70	°C
$T_{op}$	operation temperature		-10		70	°C
$T_{stg}$	storage temperature		-40		70	°C
<b>Weight</b>				4		g
$F_c$	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	9.4			mm
$d_{Spb/Appb}$		terminal to backside	5.6			mm

### Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	CS20-25moT1-TUB	CS20-25moT1	Tube	30	CS20-25moT1-TUB

### Outlines TO-268AA (D<sup>3</sup>Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.90	5.10	0.193	0.201
A1	2.70	2.90	0.106	0.114
A2	0.02	0.25	0.001	0.100
b	1.15	1.45	0.045	0.057
b2	1.90	2.10	0.075	0.083
C	0.40	0.65	0.016	0.026
C2	1.45	1.60	0.057	0.063
D	13.80	14.00	0.543	0.551
D1	12.40	12.70	0.488	0.500
E	15.85	16.05	0.624	0.632
E1	13.30	13.60	0.524	0.535
e	5.45 BSC		0.215 BSC	
H	18.70	19.10	0.736	0.752
L	2.40	2.70	0.094	0.106
L1	1.20	1.40	0.047	0.055
L2	1.00	1.15	0.039	0.045
L3	0.25 BSC		0.100 BSC	
L4	3.80	4.10	0.150	0.161

RECOMMENDED MINIMUM FOOT PRINT FOR SMD